

isc Silicon NPN Power Transistor

2SC2233

DESCRIPTION

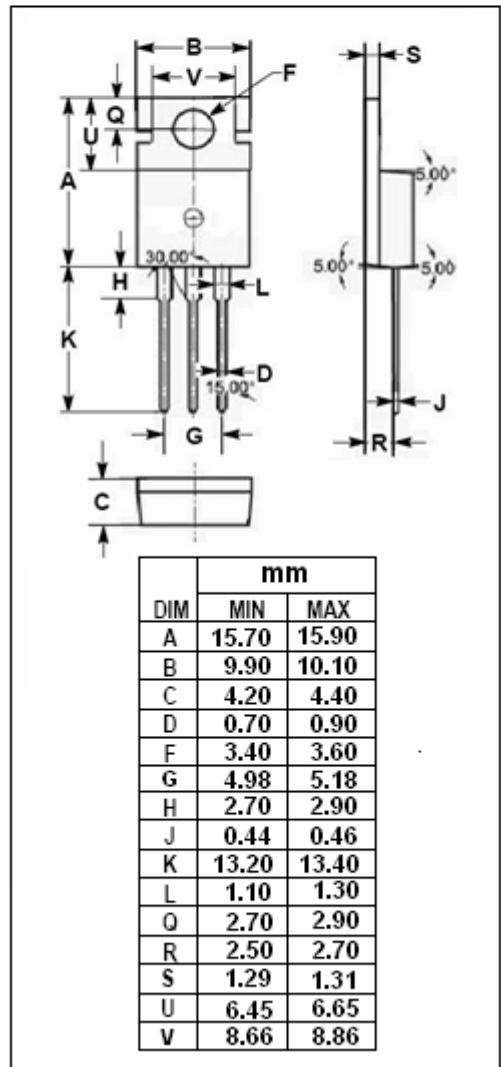
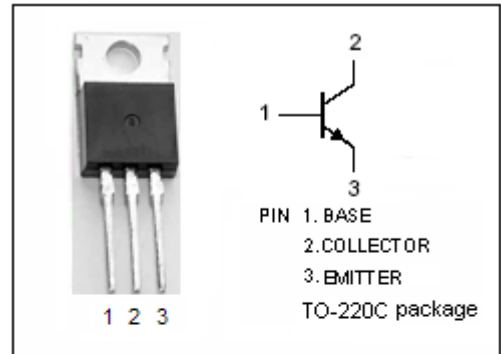
- Collector-Emitter Breakdown Voltage-
: $V_{CEO} = 60V(\text{Min})$
- DC Current Gain-
: $h_{FE} = 30(\text{Min})@ (V_{CE} = 5V, I_C = 1A)$
- High Collector Current
- High Collector Power Dissipation

APPLICATIONS

- TV Horizontal Deflection Output Application

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.5	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	40	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SC2233****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.4\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.4\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=170\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			10	μA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	30		150	
h_{FE-2}	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C=500\text{mA}; V_{CE}=5\text{V}$		8		MHz